

## 25kV 10mA HIGH VOLTAGE DIODES

G25FP is high reliability resin molded type high voltage diode in small size package which is sealed a multilayered mesa type silicon chip by epoxy resin.

### Features

- High speed switching
- High Current
- High surge resistivity for CRT discharge
- High reliability design
- High Voltage

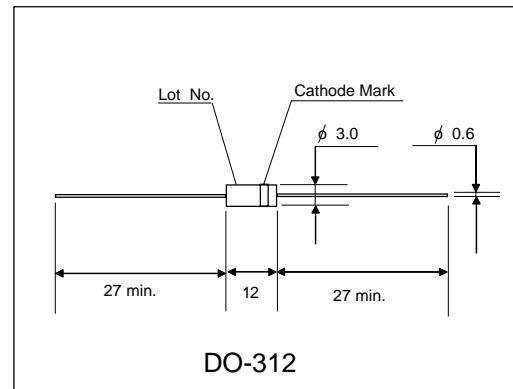
### Applications

- X light Power supply
- Laser
- Voltage doubler circuit
- Microwave emission power

### Maximum Ratings and Characteristics

- Absolute Maximum Ratings

### Outline Drawings : mm



### Cathode Mark

Type	Mark
G25FP	

Items	Symbols	Condition	G25FP	Units
Repetitive Peak Reverse Voltage	$V_{RRM}$		25	kV
Average Output Current	$I_o$	Ta=25°C, Resistive Load	10	mA
Surge Current	$I_{FSM}$		0.8	A <sub>peak</sub>
Junction Temperature	$T_j$		125	°C
Allowable Operation Case Temperature	$T_c$		120	°C
Storage Temperature	$T_{stg}$		-40 to +125	°C

### Electrical Characteristics (Ta=25°C Unless otherwise specified)

Items	Symbols	Conditions	G25FP	Units
Maximum Forward Voltage Drop	$V_F$	at 25°C, $I_F = I_{F(AV)}$	55	V
Maximum Reverse Current	IR1	at 25°C, $V_R = V_{RRM}$	2.0	uA
	IR2	at 100°C, $V_R = V_{RRM}$	5.0	uA
Maximum Reverse Recovery Time	$T_{rr}$	at 25°C	100	nS
Junction Capacitance	$C_j$	at 25°C, $V_R = 0V, f = 1MHz$	--	pF